快捷芯
KUAIJIEXIN

KJ008N10D7

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☑ Surface-mounted package
- ☑ 100% Avalanche Tested
- ☑ $T_{J\,max}$ 175℃
- ☑ Advanced trench cell design
- ☑ MSL1

1.2 Applications

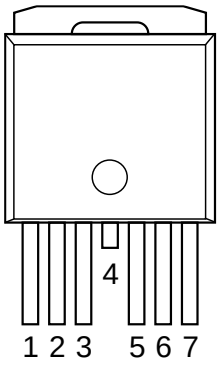
- ☑ Power Tool appliances
- ☑ BMS appliances
- ☑ High power inverter system

1.3 Quick reference

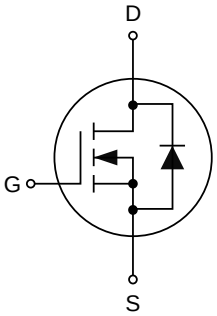
- ☑ BV≥ 100 V
- ☑ P_D ≤ 312.5 W
- ☑ I_D ≤ 468 A
- ☑ $R_{DS(ON)}$ ≤ 1.0 mΩ @V_{GS} = 10 V

2. Pin Description

Pin	Description
1	Gate(G)
2, 3	Source(S)
4	Drain(D)
5, 6, 7	Source(S)



Top View
TO263-7L



3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	T_C=25℃	100	-	V
V_{GS}	Gate-Source Voltage	T_C=25℃	-	±20	V
I_D *, ***	Drain Current (DC)	T_C=25℃, V_{GS}=10 V	-	468	A
		T_C=100℃, V_{GS}=10 V	-	330	A
I_{DM} *, **	Drain Current (Pulsed)	T_C=25℃, V_{GS}=10 V	-	1638	A
P_D	Power Dissipation	T_C=25℃	-	312.5	W
E_{AS}	Single Pulsed Avalanche Energy	V_{DD}=75 V, L=0.3 mH	-	2535	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	175	℃
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		-	40	℃/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		-	0.48	℃/W

Notes:

* Surface Mounted on 1 in^2 pad area, t ≤ 10 sec.

** Pulse width ≤ 300 μs, duty cycle ≤ 2%.

*** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ008N10D7	**KJ008N10D7 HYWWZZ XXXXXX-X**

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ008N10D7	**TO263-7L**	**13"**	**24 mm**	**800**

Note: KUAIJIEXIN defines “Green” as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0 V, I_{DS}=250 μA	100	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250 μA	2.5	-	3.5	V
I_{DSS}	Drain Leakage Current	V_{DS}=100 V, V_{GS}=0 V	-	-	1	μA
I_{GSS}	Gate Leakage Current	V_{DS}=0 V, V_{GS}=±20 V	-	-	±100	nA
$R_{DS(ON)}$ [a]	On-State Resistance	V_{GS}=10 V, I_{DS}=50 A	-	0.8	1.0	mΩ
R_g	Gate Resistance		-	1	2	Ω
Diode Characteristics						
V_{SD} [a]	Diode Forward Voltage	V_{GS}=0 V, I_{SD}=30 A	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	V_{DS}=50 V, V_{GS}=0 V, I_{DS}=30 A, di/dt=100 A/μs	-	110	-	ns
Q_{rr}	Reverse Recovery Charge		-	300	-	nC
Dynamic Characteristics [b]						
C_{iss}	Input Capacitance	V_{DS}=50 V, V_{GS}=0 V, f=1 MHz	-	11900	-	pF
C_{oss}	Output Capacitance		-	5400	-	
C_{rss}	Reverse Transfer Capacitance		-	250	-	
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=50 V, V_{GEN}=10 V, R_G=6 Ω, I_{DS}=30 A	-	55	-	ns
t_r	Turn-on Rise Time		-	100	-	
$t_{d(off)}$	Turn-off Delay Time		-	160	-	
t_f	Turn-off Fall Time		-	110	-	
Gate Charge Characteristics [b]						
Q_g	Total Gate Charge	V_{DS}=50 V, V_{GS}=10 V, I_{DS}=30 A	-	180	-	nC
Q_{gs}	Gate-Source Charge		-	70	-	
Q_{gd}	Gate-Drain Charge		-	60	-	

Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

b. Guaranteed by design, not subject to production testing.

7. Typical Characteristics

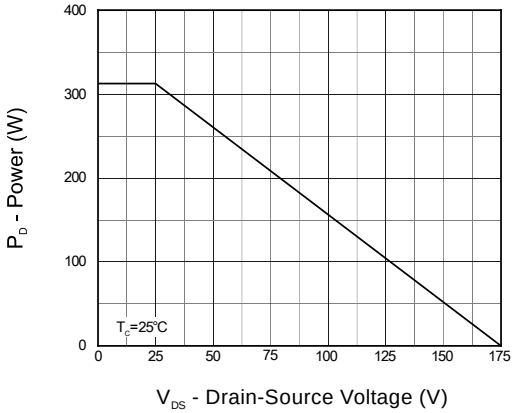


Fig 1. Output Characteristics

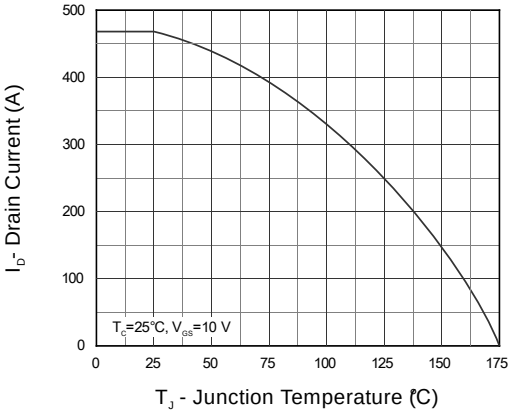


Fig 2. Current Capability

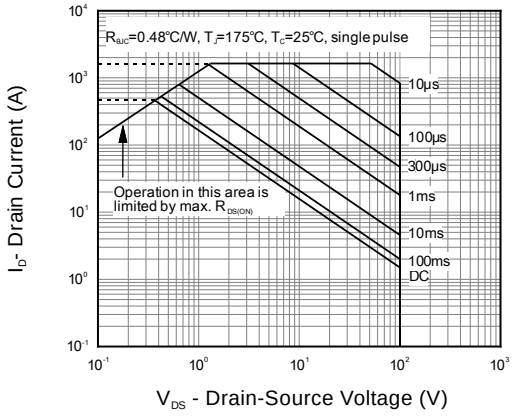


Fig 3. Safe Operation Area

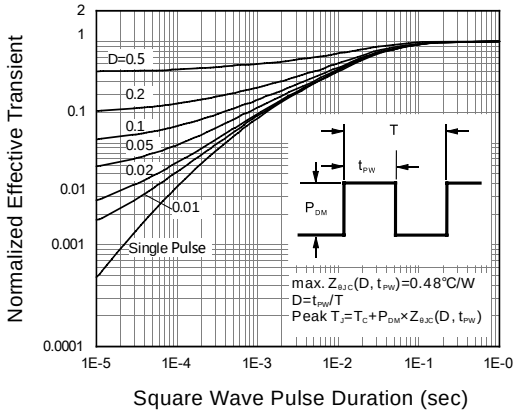


Fig 4. Transient Thermal Impedance

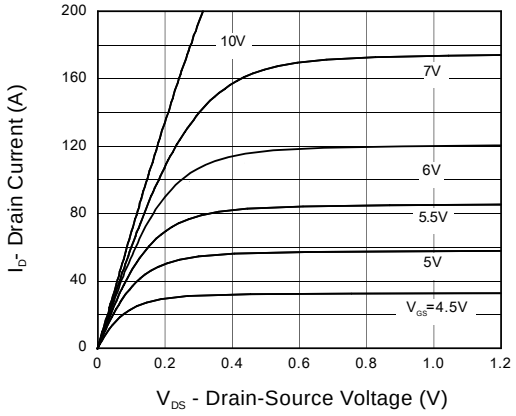


Fig 5. Output Characteristics

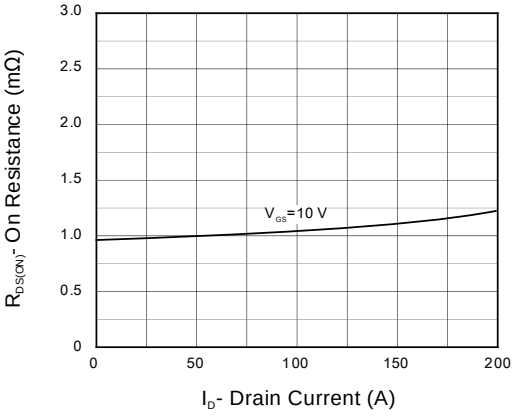


Fig 6. On Resistance

7. Typical Characteristics (cont.)

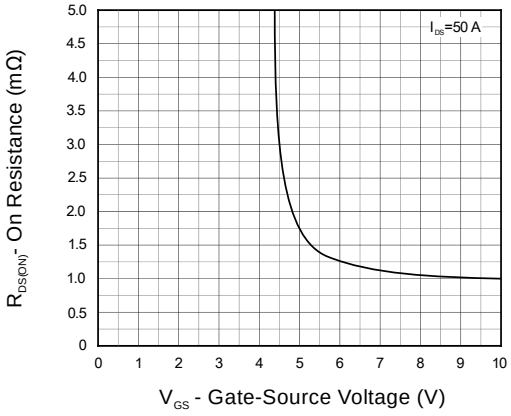


Fig 7. Transfer Characteristics

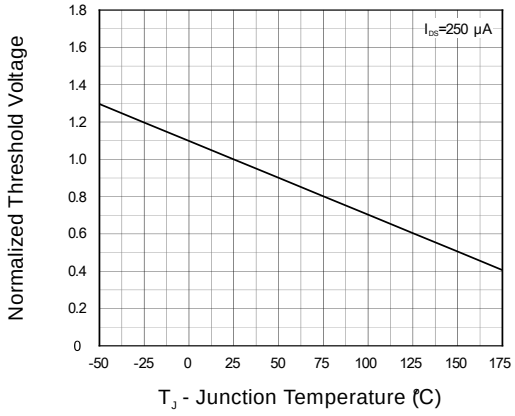


Fig 8. Normalized Threshold Voltage

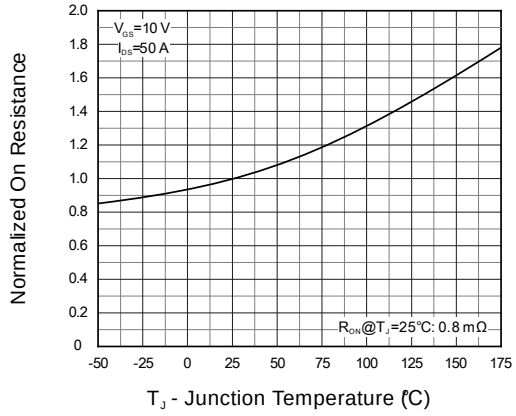


Fig 9. Normalized On Resistance

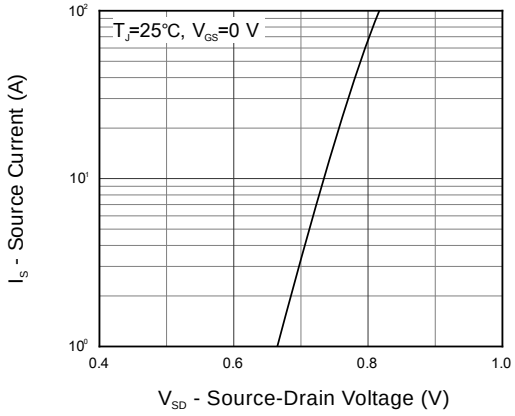


Fig 10. Diode Forward Current

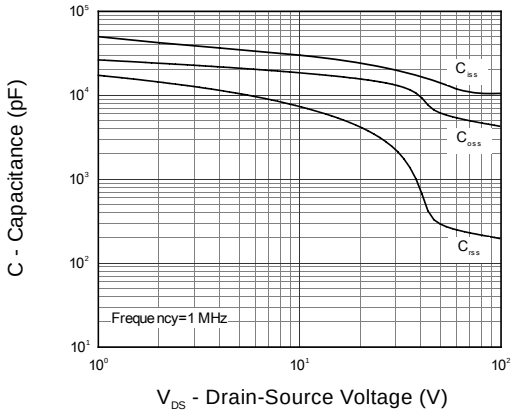


Fig 11. Capacitance

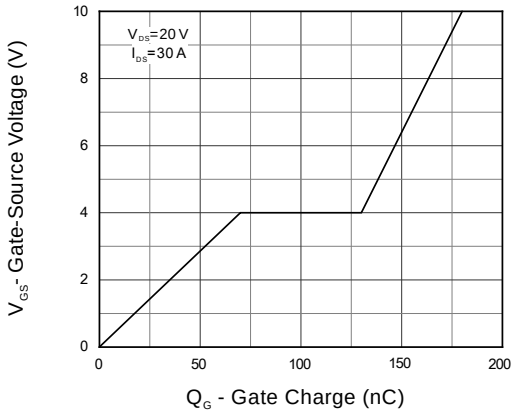
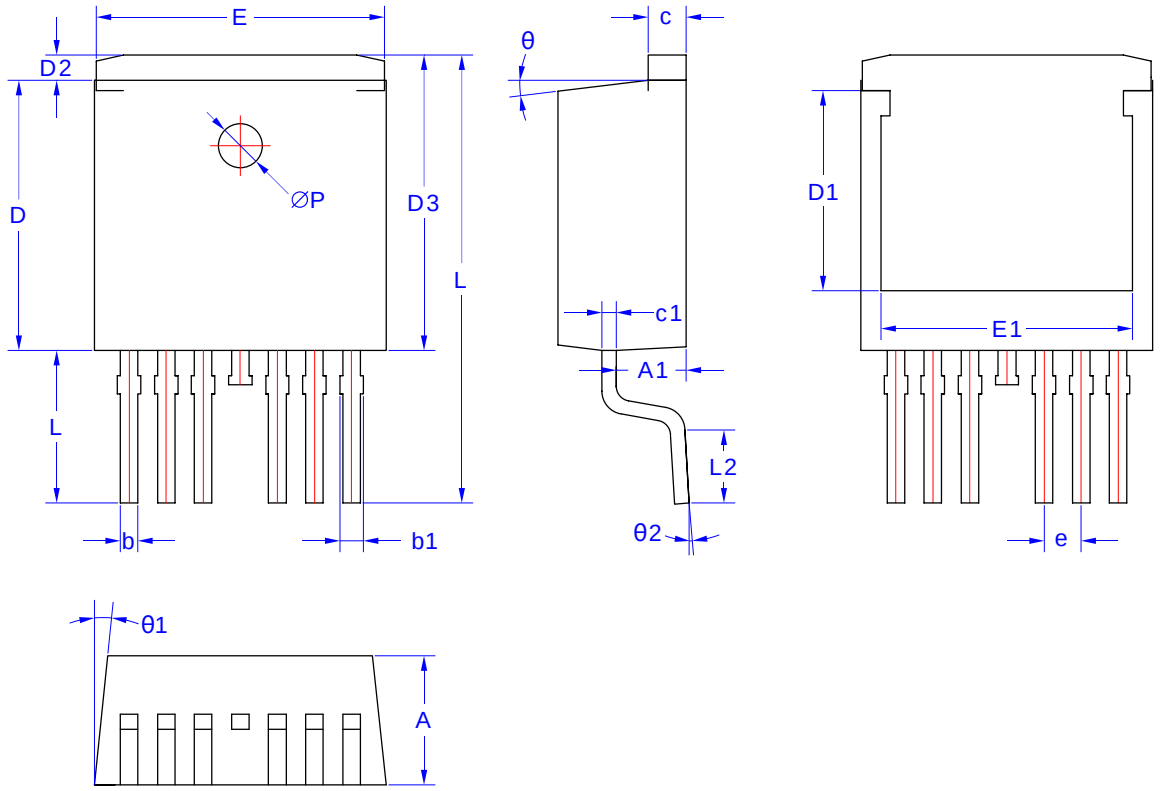


Fig 12. Gate Charge

8. Package Dimensions

TO263-7L Package



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A	4.20	4.40	4.60
A1	2.30	2.40	2.50
b	0.50	0.60	0.70
b1	0.60	0.70	0.80
c	1.25	1.30	1.35
c1	0.45	0.50	0.55
D	9.05	9.25	9.45
D1	6.65	6.85	7.05
D2	0.65	0.85	1.05
D3	9.90	10.10	10.30

Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
E	9.80	10.00	10.20
E1	8.50	8.60	8.70
e	-	1.27 BSC	-
L	14.90	15.10	15.40
L1	4.80	5.00	5.20
L2	2.30	2.50	2.70
θ	5°	7°	10°
θ1	3°	5°	8°
θ2	0°	-	8°
ΦP	-	1.50	-